

L Number	Hits	Search Text	DB	Time stamp
1	0	(semiconductor adj device) and (back adj gate adj electrode) and (field adj effect adj transistor) and (electrical adj charge) and (threshold adj volatge) and channel and region and (potential adj lying)	USPAT	2003/03/19 11:42
2	0	(semiconductor adj device) and (back adj gate adj electrode) and (field adj effect adj transistor) and (threshold adj volatge) and channel and region and potential	USPAT	2003/03/19 11:40
3	36	(semiconductor adj device) and (back adj gate adj electrode) and (field adj effect adj transistor) and (threshold adj voltage) and channel and region and potential	USPAT	2003/03/19 11:40
4	0	(semiconductor adj device) and (back adj gate adj electrode) and (field adj effect adj transistor) and (threshold adj voltage) and channel and region and potential	USPAT	2003/03/19 12:01
5	2	(semiconductor adj device) and (back adj gate adj electrode) and (field adj effect adj transistor) and (electrical adj charge) and (threshold adj voltage) and channel and region and (potential adj lying)	USPAT	2003/03/19 11:43
6	2	((semiconductor adj device) and (back adj gate adj electrode) and (field adj effect adj transistor) and (electrical adj charge) and (threshold adj voltage) and channel and region or field or effect or transistor or semiconductor or insulating or dielectric or channel or electrical or electrically or back or gate or electrode or opposing or relationship or region or applying or potential or lying or direction or induce or charge or conduction or conductive or type or body or portion or increase or threshold or voltage or stabilize or source or drain or withstand or aging or state or leakage or current or time or decreased or decreased or increased or circuit or block or high or speed or low or partial or depletion or test or device or driving)	USPAT	2003/03/19 11:44
7	2	(semiconductor adj device) and (back adj gate adj electrode) and (field adj effect adj transistor) and (threshold adj voltage) and channel and region and potential and (electrical adj charge)	USPAT	2003/03/19 12:16
8	2	((semiconductor adj device) and (back adj gate adj electrode) and (field adj effect adj transistor) and (threshold adj voltage) and channel and region and potential and (electrical adj charge)) and (partial or depletion or type or transistor or field effect or insulating or dielectric)	USPAT	2003/03/19 12:06
9	258	438/167	USPAT	2003/03/19 12:17
10	61	438/169	USPAT	2003/03/19 12:17
11	74	438/171	USPAT	2003/03/19 12:17
12	274	438/172	USPAT	2003/03/19 12:17
13	153	438/174	USPAT	2003/03/19 12:17
14	76	438/189	USPAT	2003/03/19 12:17
15	99	438/190	USPAT	2003/03/19 12:17
16	903	438/197	USPAT	2003/03/19 12:17
17	111	438/194	USPAT	2003/03/19 12:17
18	681	438/289	USPAT	2003/03/19 12:17
19	437	438/309	USPAT	2003/03/19 12:17
20	242	438/311	USPAT	2003/03/19 12:17
21	898	438/381	USPAT	2003/03/19 12:17
-	1	("6392277").PN.	USPAT	2003/03/19 12:18
-	1	("6063686").PN.	USPAT	2003/03/19 12:18
-	1	("6043536").PN.	USPAT	2003/03/19 09:58
-	1	(("6392277").PN.) and (TFT or field or effect or transistor or semiconductor or insulating or dielectric or channel or electrical or electrically or back or gate or electrode or opposing or relationship or region or applying or potential or lying or direction or induce or charge or conduction or conductive or type or body or portion or increase or threshold or voltage or stabilize or source or drain or withstand or aging or state or leakage or current or time or decreased or decreased or increased or circuit or block or high or speed or low or partial or depletion or test or device or driving)	USPAT	2003/03/19 09:58
-			USPAT	2003/03/19 11:00
-			USPAT	2003/03/19 10:12

1	(("6063686").PN.) and (TFT or field or effect or transistor or semiconductor or insulating or dielectric or channel or electrical or electrically or back or gate or electrode or opposing or relationship or region or applying or potential or lying or direction or induce or charge or conduction or conductive or type or body or portion or increase or threshold or voltage or stabilize or source or drain or withstand or aging or state or leakage or current or time or decreased or decrease or increased or circuit or block or high or speed or low or partial or depletion or test or device or driving)	USPAT	2003/03/19 11:00
1	("6043536").PN.	USPAT	2003/03/19 11:00
1	(("6043536").PN.) and (TFT or field or effect or transistor or semiconductor or insulating or dielectric or channel or electrical or electrically or back or gate or electrode or opposing or relationship or region or applying or potential or lying or direction or induce or charge or conduction or conductive or type or body or portion or increase or threshold or voltage or stabilize or source or drain or withstand or aging or state or leakage or current or time or decreased or decrease or increased or circuit or block or high or speed or low or partial or depletion or test or device or driving)	USPAT	2003/03/19 11:47

3/19/03